#### EE 42 Introduction to Electronics for **Computer Science**



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# Problem Set # 12 Due:1 PM Dec 3rd, 2003 in box in 240 Cory

#### **12.1 Diode Model Comparison**

Gallium arsenide diodes are pn-junctions that use a different substrate material, resulting in different diode characteristics. Suppose for this problem only that all diodes carry a large signal voltage of 1.4V, and have a saturation current  $I_0 = 10^{-25}$ .

a) Given the provided gallium arsenide diode circuit to the right, draw a sketch of the IV characteristic of the diode using the exponential equation provided in lecture.

1k

Then, use load line analysis to determine the operating point of the circuit.

b) Repeat the above exercise, this time using the large signal model of the diode.

### 12.2 Usage of Diodes in Circuits

Use the circuit provided to the right. Assume the provided diode is silicon.

- a) Assuming that the diode in the circuit acts as a perfect rectifier, and that the input voltage source generates a square wave with a frequency of 1kHz, a high voltage of 100mV and a low voltage of 0, draw a sketch of the voltage on the output resistor over a 10ms interval.
- b) Repeat part (a), using the large signal diode model.
- c) What kind of circuit is this? What kinds of applications could it be used for?

## 12.3 IC Resistors, MOS as Voltage Controlled Resistors

- a) Suppose a silicon resistor with a Group III dopant concentration of  $10^{16}$  cm<sup>-3</sup>. If the resistor is sized at 9µm length, 3µm width and 1µm thickness, what is the resistance? (Be sure to use the mobility values provided in lecture). Determine also the sheet resistance of this resistor.
- b) Suppose you have a MOS transistor or capacitor where the oxide thickness is 70 nm. Using the notion that capacitance is  $Cox = \varepsilon A/d$ , where A represents cross-sectional area and d represents thickness, and determine the capacitance across the gate of the transistor (determine capacitance of the oxide) per unit area.
- c) It is often the case that when the transistor is biased at an operating voltage, the equation  $Q = (V - V_T) C$  for some range of input voltages V, given a threshold  $V_T = 0.43 V$  and total gate capacitance C. If the transistor gate has a 360 nm width and a 180 nm length, what is the total charge in the channel of the transistor?
- d) Use this amount of mobile charge and the fact that mobility is the standard set of numbers from lecture, and calculate the resistance of the MOSFET. Determine how resistance would vary from NMOS to PMOS.
- e) If this were NMOS, what would be the size ratio of an equivalent resistance PMOS?

